



STP200NF03

STB200NF03 STB200NF03-1

N-CHANNEL 30V - 0.0032 Ω - 120A D²PAK/I²PAK/TO-220
STripFET™ II POWER MOSFET

AUTOMOTIVE SPECIFIC

TYPE	V _{DSS}	R _{DS(on)}	I _D
STB200NF03/-1	30 V	<0.0036 Ω	120 A(**)
STP200NF03	30 V	<0.0036 Ω	120 A(**)

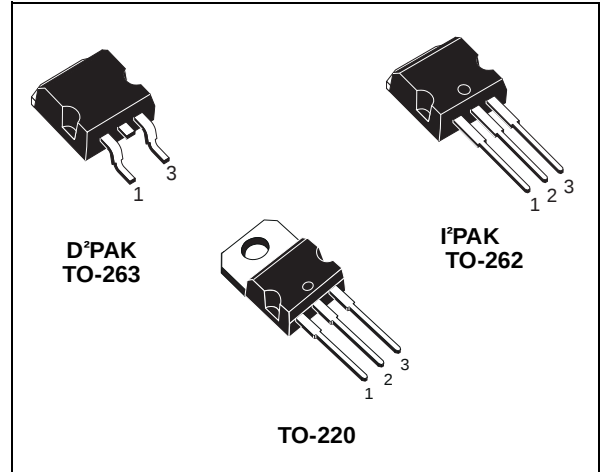
- TYPICAL R_{DS(on)} = 0.0032 Ω
- STANDARD THRESHOLD DRIVE
- 100% AVALANCHE TESTED

DESCRIPTION

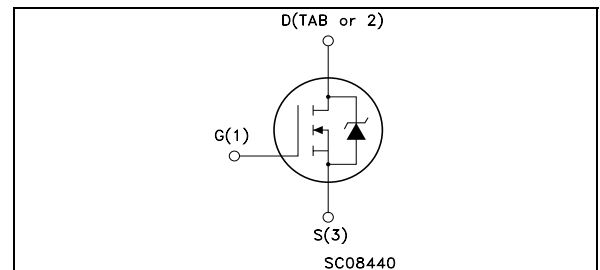
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- HIGH CURRENT, HIGH SWITCHING SPEED
- DC-DC & DC-AC CONVERTERS
- SOLENOID AND RELAY DRIVERS



INTERNAL SCHEMATIC DIAGRAM



Ordering Information

SALES TYPE	MARKING	PACKAGE	PACKAGING
STB200NF03T4	B200NF03	D ² PAK	TAPE & REEL
STP200NF03	P200NF03	TO-220	TUBE
STB200NF03-1	B200NF03	I ² PAK	TUBE

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	30	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 k Ω)	30	V
V _{GS}	Gate- source Voltage	± 20	V
I _D (**)	Drain Current (continuous) at T _C = 25°C	120	A
I _D	Drain Current (continuous) at T _C = 100°C	120	A
I _{DM} (•)	Drain Current (pulsed)	480	A
P _{tot}	Total Dissipation at T _C = 25°C	300	W
	Derating Factor	2.0	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	1.5	V/ns
E _{AS} (2)	Single Pulse Avalanche Energy	1.45	J
T _{stg}	Storage Temperature	-55 to 175	°C
T _j	Operating Junction Temperature		

(•) Pulse width limited by safe operating area.

(**) Current Limited by Package

(1) I_{SD} ≤ 120A, di/dt ≤ 400A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}

(2) Starting T_j = 25 °C, I_D = 60 A, V_{DD} = 25 V

STB200NF03/-1 STP200NF03**THERMAL DATA**

Rthj-case	Thermal Resistance Junction-case	Max	0.5	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	62.5	°C/W
Rthj-pcb	Thermal Resistance Junction-pcb	Max	see curve on page 6	°C/W
T _I	Maximum Lead Temperature For Soldering Purpose (for 10 sec. 1.6 mm from case)	Typ	300	°C

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)**OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA V _{GS} = 0	30			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _C = 125°C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20V			±100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 µA	2		4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 60 A		0.0032	0.0036	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} = 15 V I _D = 60 A		200		S
C _{iss} C _{oss} C _{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		4950 1750 280		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 15\text{ V}$ $I_D = 60\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 3)		30 195		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 24\text{ V}$ $I_D = 120\text{ A}$ $V_{GS} = 10\text{ V}$		113 32 41	140	nC nC nC

SWITCHING OFF

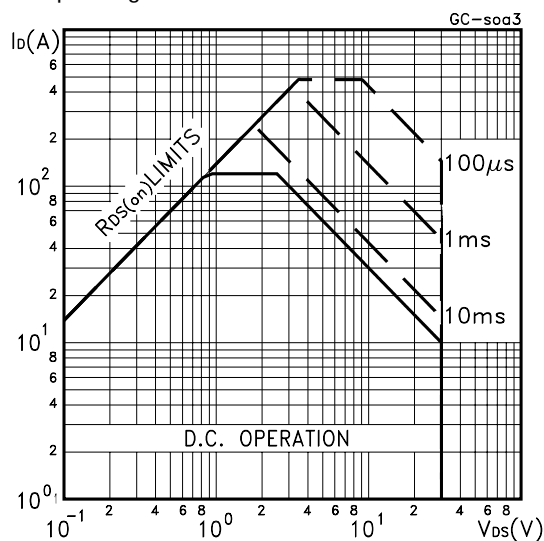
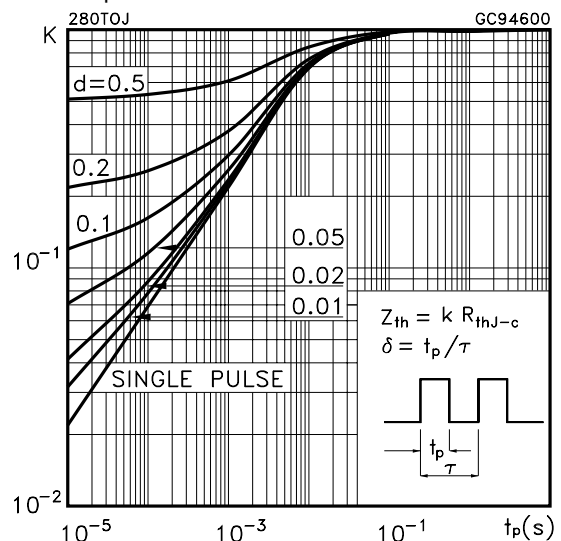
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 15\text{ V}$ $I_D = 60\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 3)		75 60		ns ns

SOURCE DRAIN DIODE

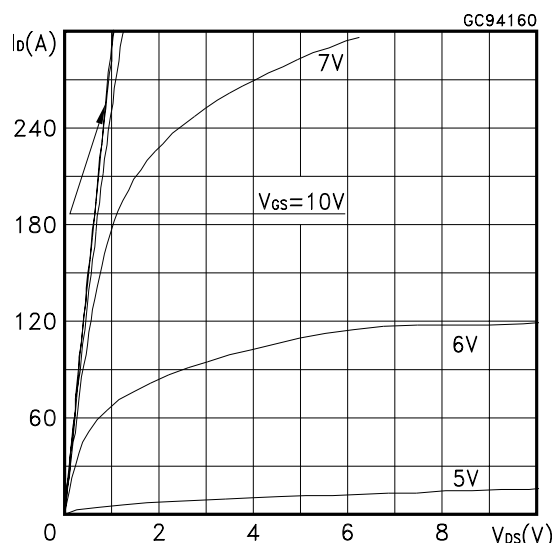
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(*)}$	Source-drain Current Source-drain Current (pulsed)				120 480	A A
$V_{SD}^{(*)}$	Forward On Voltage	$I_{SD} = 120\text{ A}$ $V_{GS} = 0$			1.3	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 120\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 25\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		70 170 5		ns nC A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

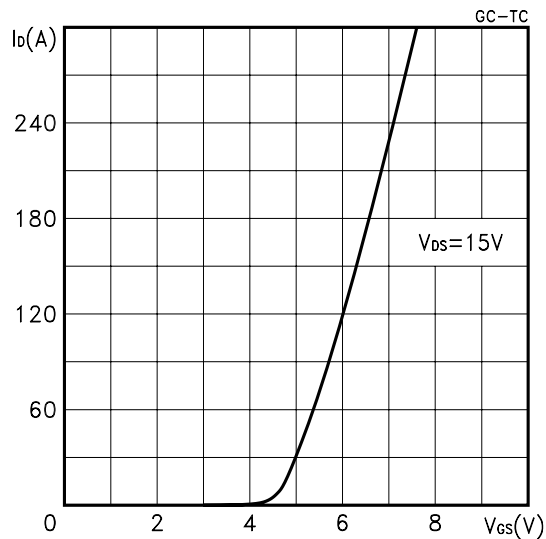
(●) Pulse width limited by safe operating area.

Safe Operating Area**Thermal Impedance**

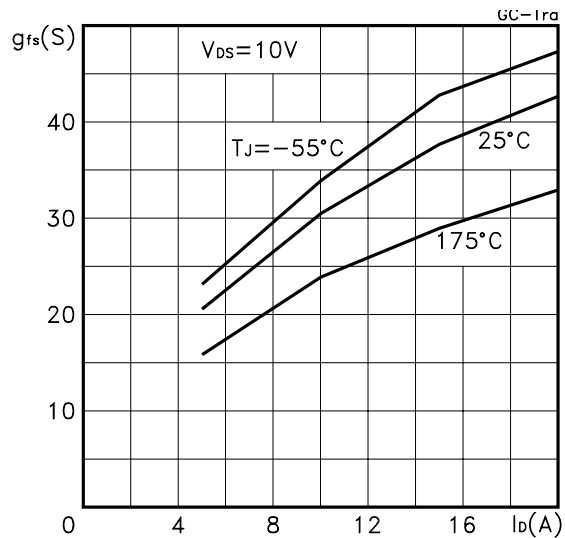
Output Characteristics



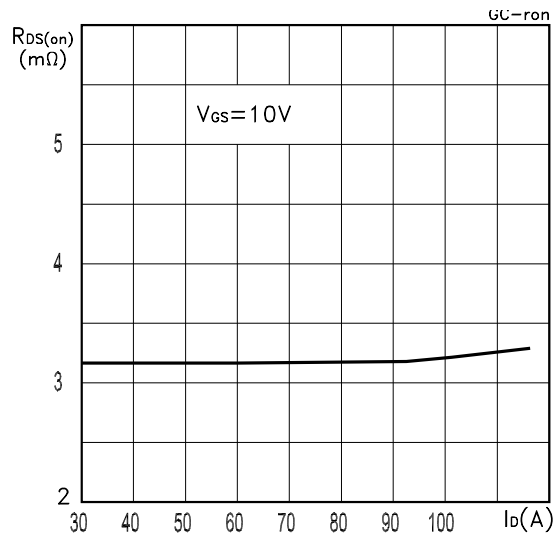
Transfer Characteristics



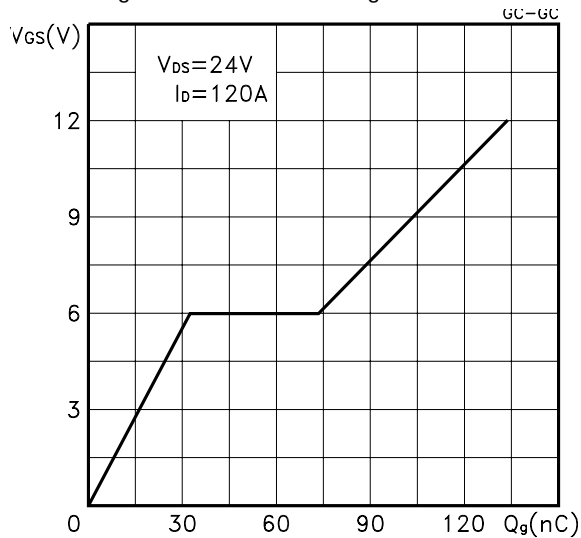
Transconductance



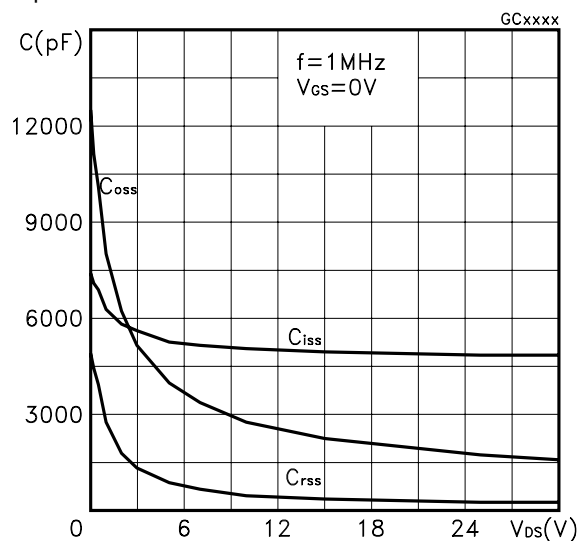
Static Drain-source On Resistance



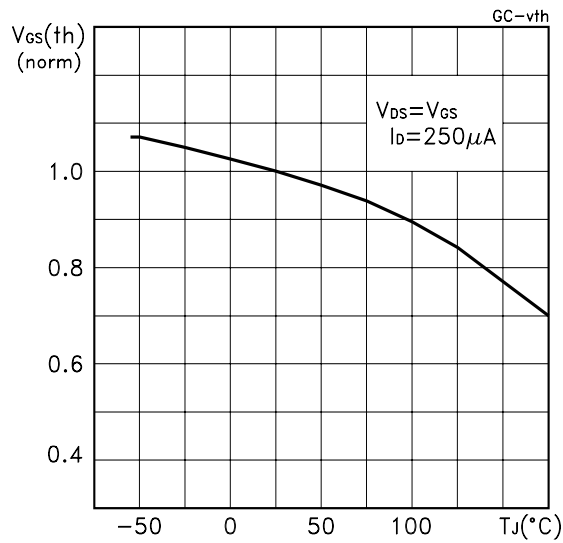
Gate Charge vs Gate-source Voltage



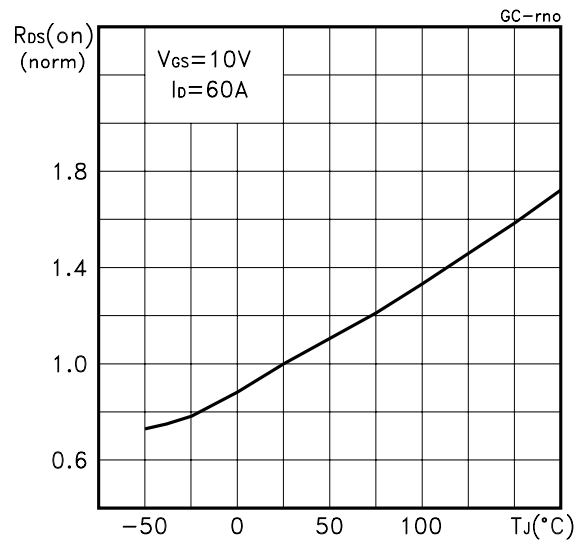
Capacitance Variations



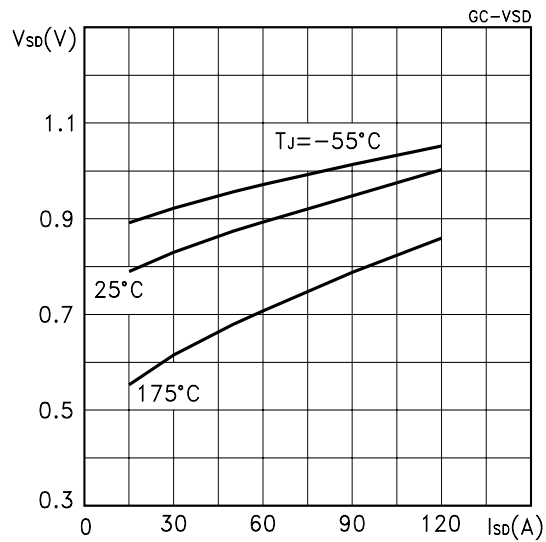
Normalized Gate Threshold Voltage vs Temperature



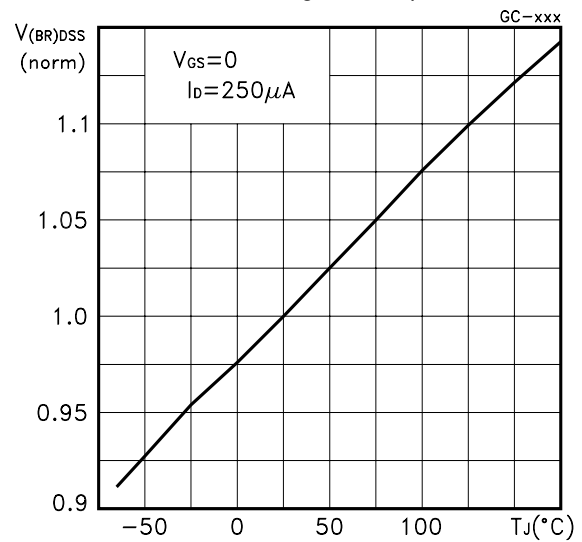
Normalized on Resistance vs Temperature



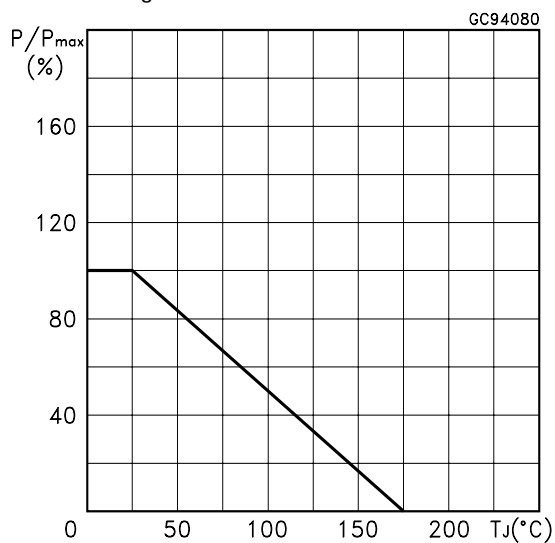
Source-drain Diode Forward Characteristics



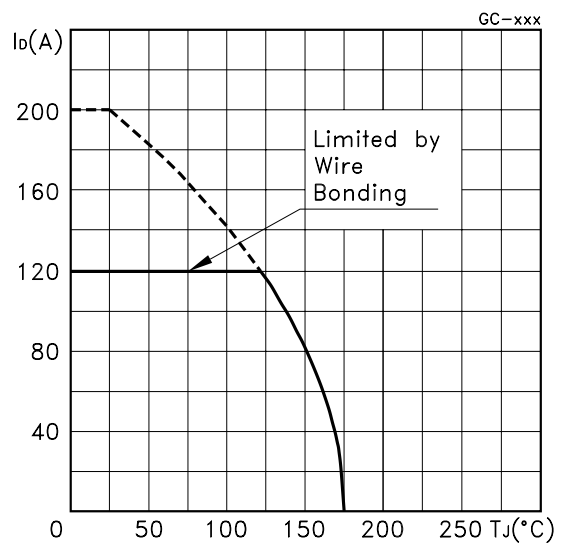
Normalized Breakdown Voltage vs Temperature.



Power Derating vs Tc

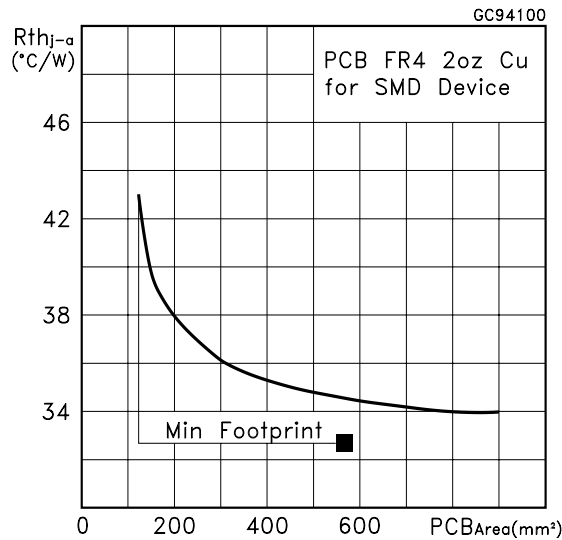


Max Id Current vs Tc.

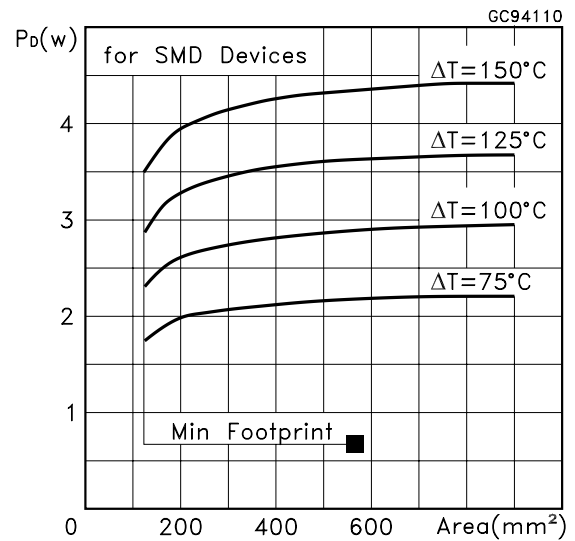


STB200NF03/-1 STP200NF03

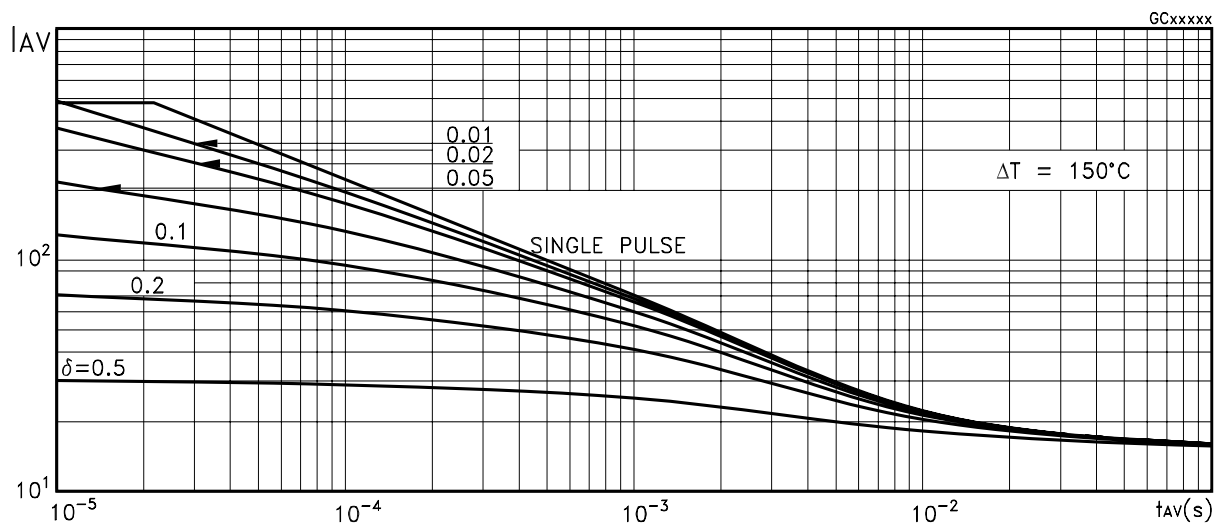
Thermal Resistance R_{thj-a} vs PCB Copper Area



Max Power Dissipation vs PCB Copper Area



Allowable I_{AV} vs. Time in Avalanche



The previous curve gives the safe operating area for unclamped inductive loads, single pulse or repetitive, under the following conditions:

$$P_{D(AVE)} = 0.5 * (1.3 * BV_{DSS} * I_{AV})$$

$$E_{AS(AR)} = P_{D(AVE)} * t_{AV}$$

Where:

I_{AV} is the Allowable Current in Avalanche

$P_{D(AVE)}$ is the Average Power Dissipation in Avalanche (Single Pulse)

t_{AV} is the Time in Avalanche

To derate above 25 °C, at fixed I_{AV} , the following equation must be applied:

$$I_{AV} = 2 * (T_{jmax} - T_{CASE}) / (1.3 * BV_{DSS} * Z_{th})$$

Where:

$Z_{th} = K * R_{th}$ is the value coming from Normalized Thermal Response at fixed pulse width equal to T_{AV} .

SPICE THERMAL MODEL

Parameter	Node	Value
CTHERM1	5 - 4	0.011
CTHERM2	4 - 3	0.0012
CTHERM3	3 - 2	0.05
CTHERM4	2 - 1	0.1
RTHERM1	5 - 4	0.09
RTHERM2	4 - 3	0.02
RTHERM3	3 - 2	0.11
RTHERM4	2 - 1	0.17

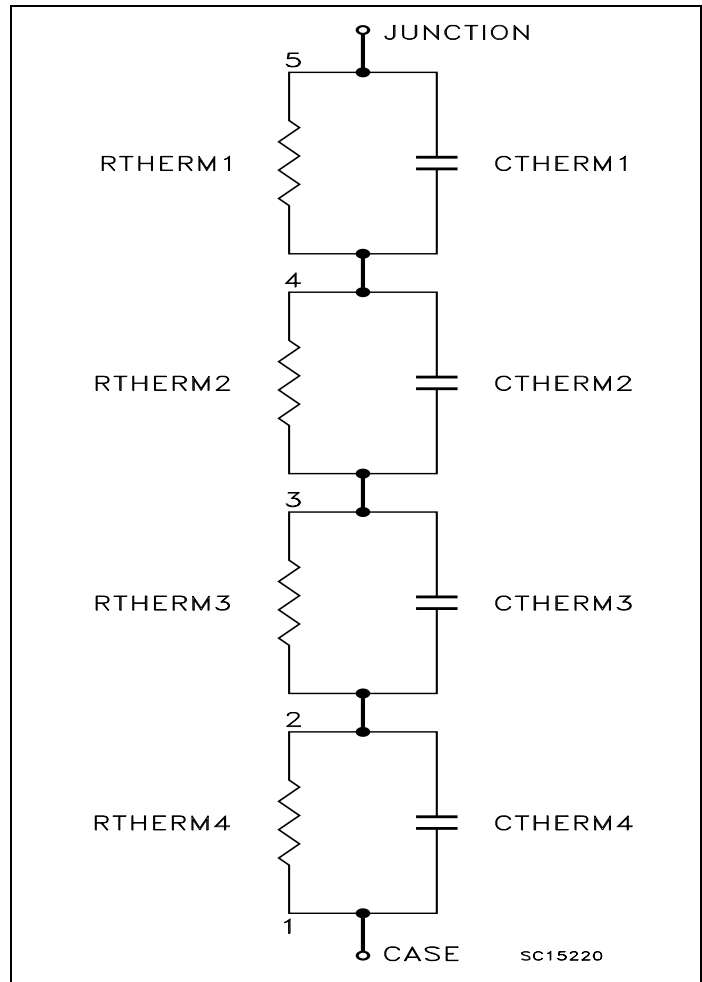


Fig. 1: Unclamped Inductive Load Test Circuit

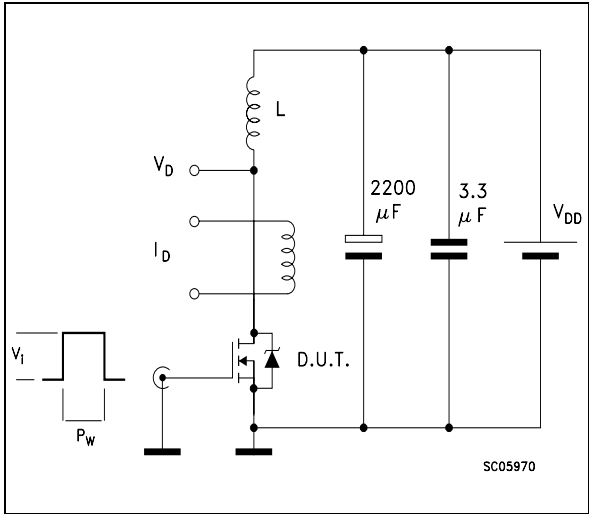


Fig. 2: Unclamped Inductive Waveform

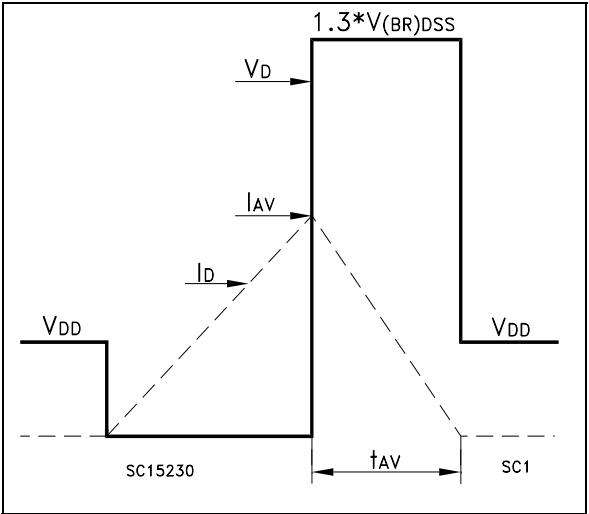


Fig. 3: Switching Times Test Circuits For Resistive Load

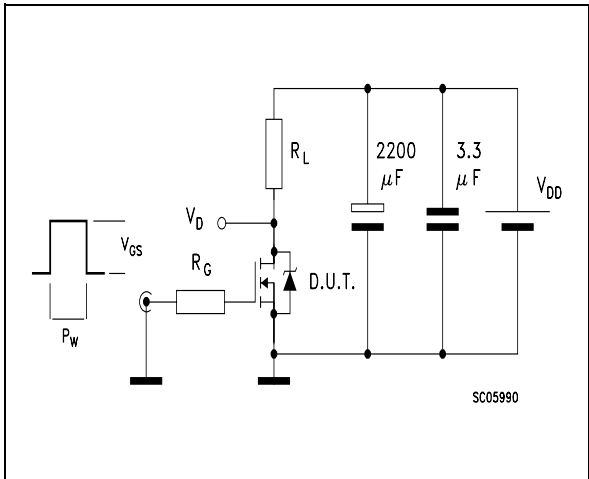


Fig. 3.1: Switching Time Waveform

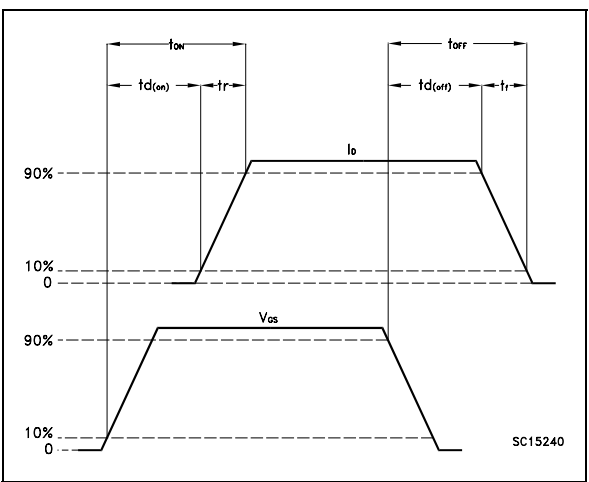


Fig. 4: Gate Charge Test Circuit

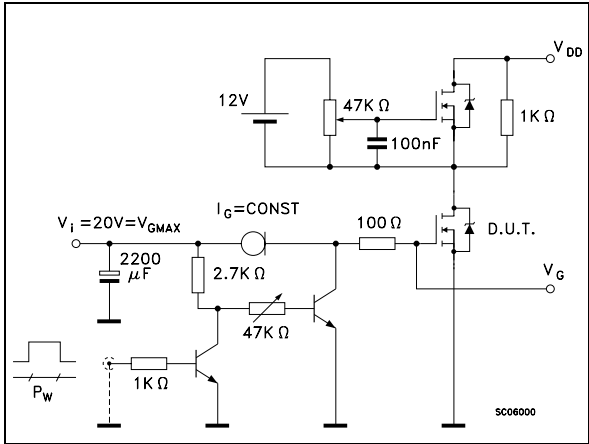


Fig. 4.1: Gate Charge Test Waveform

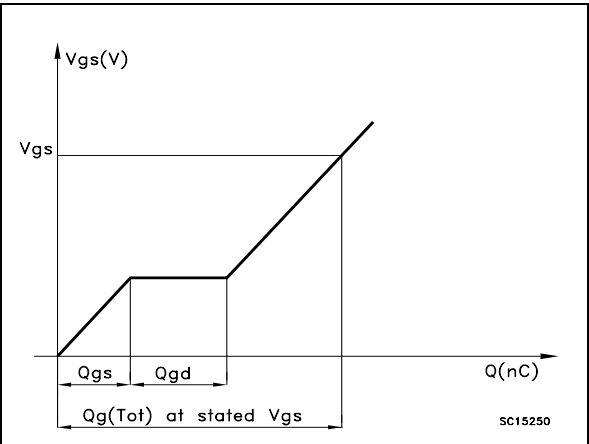
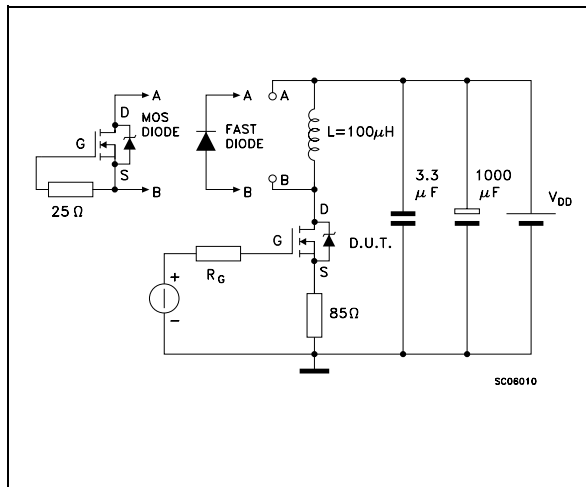
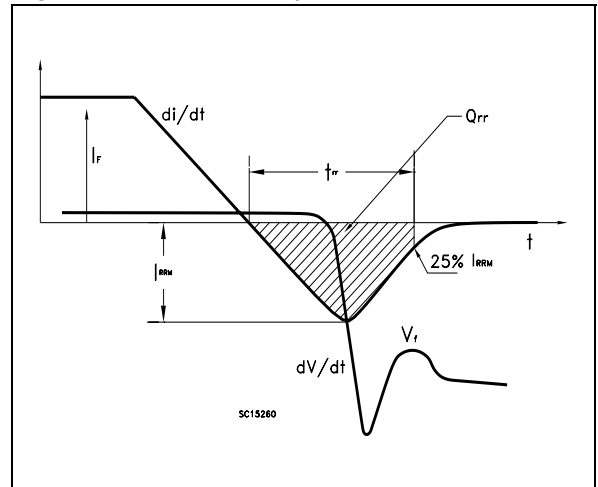
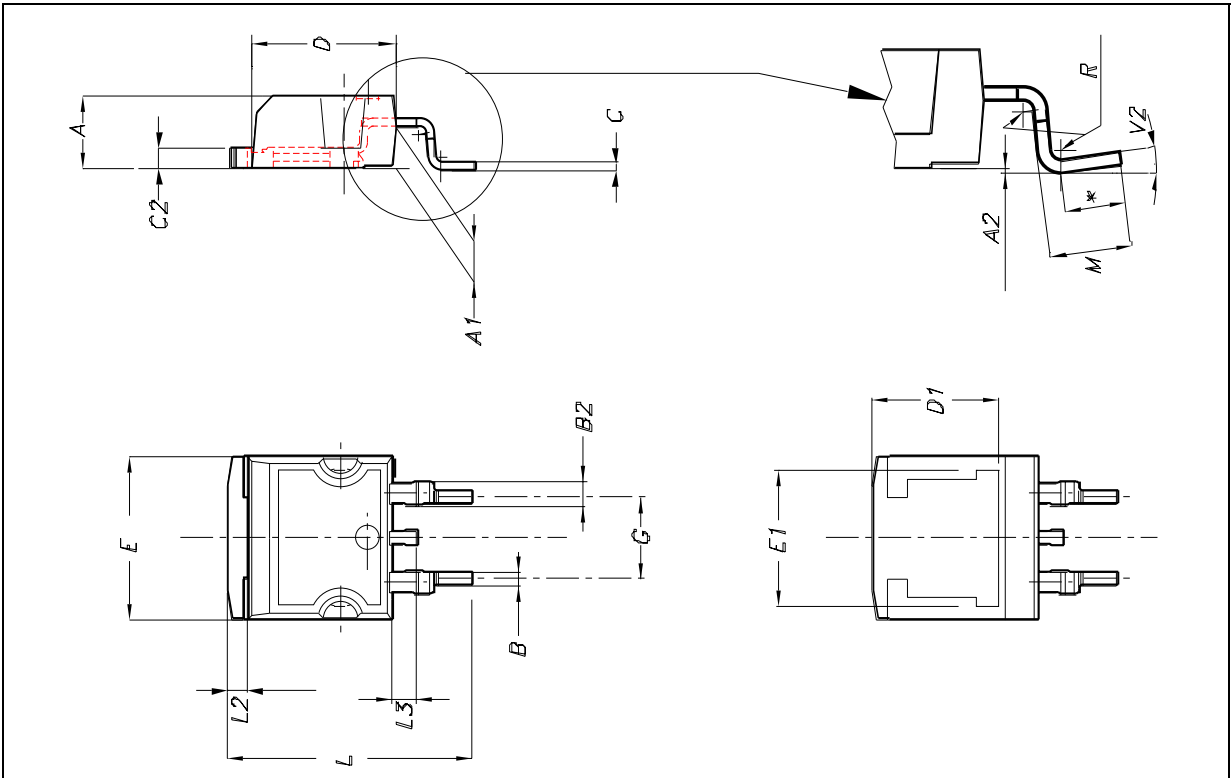


Fig. 5: Diode Switching Test Circuit**Fig. 5.1:** Diode Recovery Times Waveform

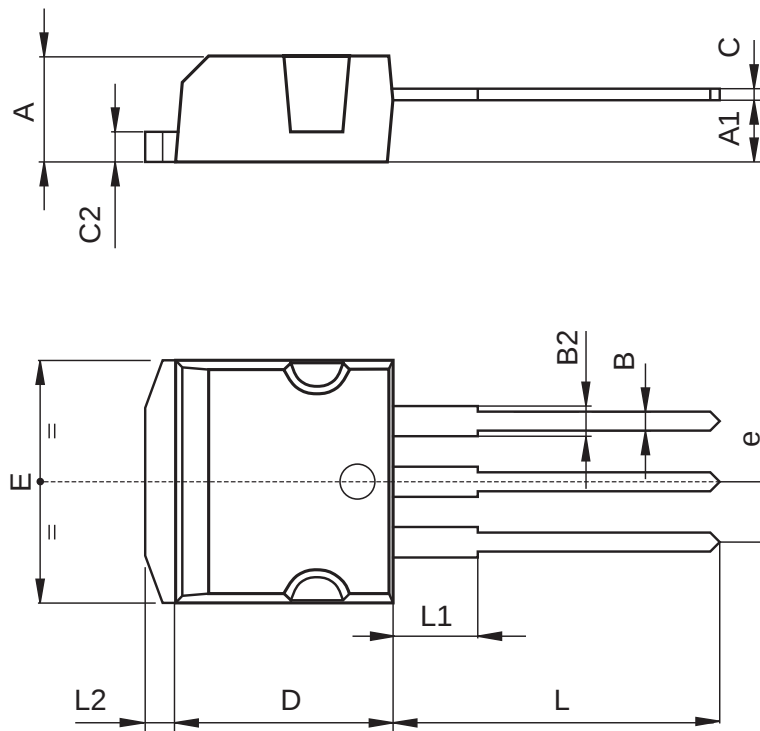
D²PAK MECHANICAL DATA

DIM.	mm.			inch.		
	MIN.	TYP.	MAX.	MIN.	TYP.	TYP.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.028		0.037
B2	1.14		1.7	0.045		0.067
C	0.45		0.6	0.018		0.024
C2	1.21		1.36	0.048		0.054
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.394		0.409
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.591		0.624
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.069
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		8°	0°		8°



TO-262 (I²PAK) MECHANICAL DATA

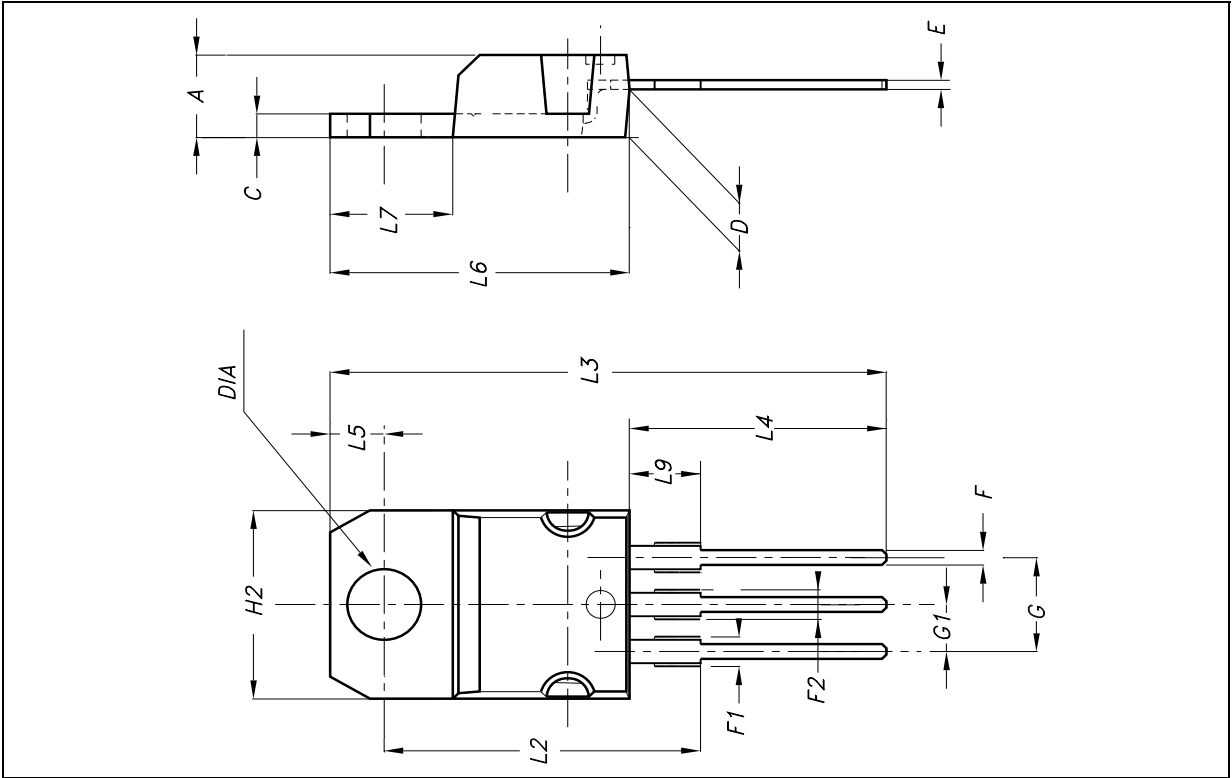
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
e	2.4		2.7	0.094		0.106
E	10		10.4	0.393		0.409
L	13.1		13.6	0.515		0.531
L1	3.48		3.78	0.137		0.149
L2	1.27		1.4	0.050		0.055

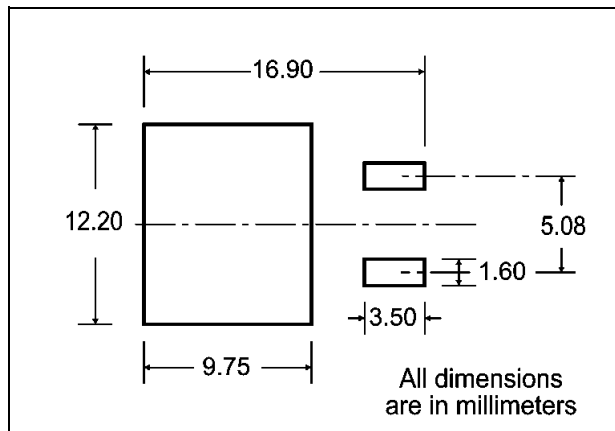
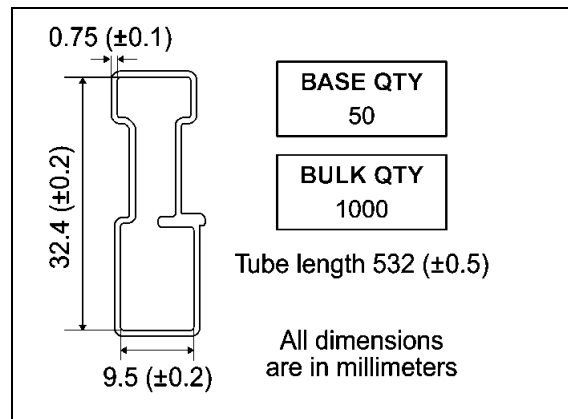
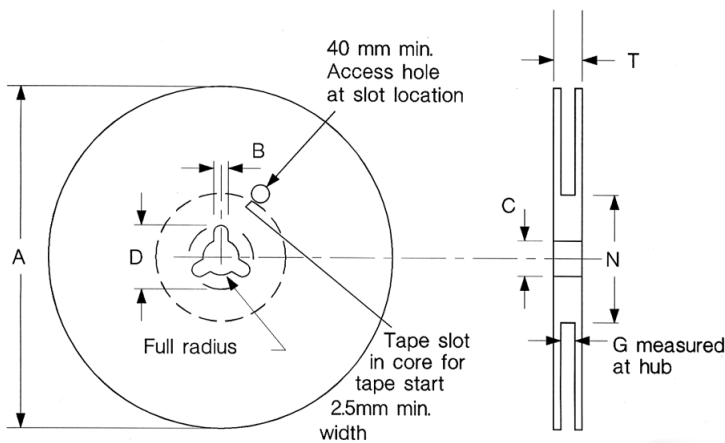


P011P5/E

TO-220 MECHANICAL DATA

DIM.	mm.			inch.		
	MIN.	TYP.	MAX.	MIN.	TYP.	TYP.
A	4.4		4.6	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.40		2.70	0.094		0.106
H2	10		10.40	0.393		0.409
L2		16.40			0.645	
L3		28.90			1.137	
L4	13		14	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.20		6.60	0.244		0.260
L9	3.50		3.93	0.137		0.154
DIA	3.75		3.85	0.147		0.151



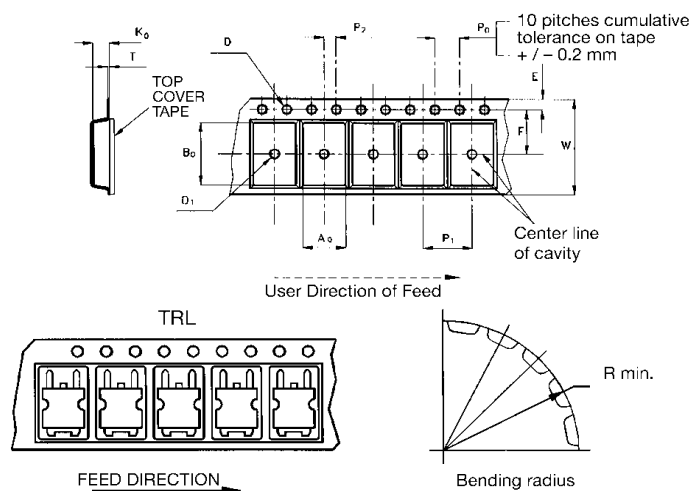
D2PAK FOOTPRINT**TUBE SHIPMENT (no suffix)*****TAPE AND REEL SHIPMENT (suffix "T4")*****REEL MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956



* on sales type



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